

SOT-23 Plastic-Encapsulate Transistors

M28S TRANSISTOR (NPN)

FEATURES

Power dissipation

Pcm:0.625W (Tamb=25℃)

MARKING:28S

SOT-23

1. BASE
2. EMITTER
3. COLLECTOR



MAXIMUM RATINGS (TA=25℃ unless otherwise noted)

Symbol (符号)	Parameter (参数名称)	Value (额定值)	Units (单位)
VCBO	Collector-Base Voltage (集电极-基极电压)	40	V
VCEO	Collector-Emitter Voltage (集电极-发射极电压)	20	V
VEBO	Emitter-Base Voltage (发射极-基极电压)	6	V
IC	Collector Current -Continuous (集电极电流)	1	A
PC	Collector Power Dissipation (耗散功率)	0.625	W
Tj	Junction Temperature (结温)	150	℃
Tstg	Storage Temperature (储存温度)	-55-150	℃

ELECTRICAL CHARACTERISTICS (Tamb=25℃ unless otherwise specified)

Parameter (参数名称)	Symbol (符号)	Test conditions (测试条件)	MIN (最小值)	TYP (典型值)	MAX (最大值)	UNIT (单位)
Collector-base breakdown voltage 集电极-基极击穿电压	V(BR)CBO	IC= 100μA, IE=0	40			V
Collector-emitter breakdown voltage 集电极-发射极击穿电压	V(BR)CEO	IC= 1mA, IB=0	20			V
Emitter-base breakdown voltage 发射极-基极击穿电压	V(BR)EBO	IE=100μA, IC=0	6			V
Collector cut-off current 集电极-基极截止电流	ICBO	VCB=30 V, IE=0			1	μA
Collector cut-off current 集电极-发射极截止电流	ICEO	VCE=15V, IB=0			10	μA
Emitter cut-off current 发射极-基极截止电流	IEBO	VEB=5V, IC=0			1	μA
DC current gain 直流电流增益	hFE	VCE=1V, IC= 100mA	300		1000	
Collector-emitter saturation voltage 集电极-发射极饱和压降	VCE(sat)	IC=600mA, IB= 20mA			0.55	V
Transition frequency 特征频率	f _T	VCE=10V, IC= 50mA f=30MHz	100			MHz

CLASSIFICATION OF hFE

Range	300-500	500-700	700-1000	
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